

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

# 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM (class H2)
- Trench MOSFET technology
- AEC-Q101 qualified

## 3. Applications

- DC to DC conversion
- High-speed line driver
- Low-side load switch
- Switching circuits

# 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 25 °C		-	-	26	А
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C		-	-	19	W
Static chara	cteristics		- I				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8.5 A; T <sub>j</sub> = 25 °C		-	13	16	mΩ

# nexperia

# 5. Pinning information

Table 2	Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol					
1	D	drain		D					
2	D	drain							
3	G	gate							
4	S	source	3 8 4						
5	D	drain	Transparent top view						
6	D	drain	DFN2020MD-6 (SOT1220)	s					
7	D	drain		017aaa255					
8	S	source							

# 6. Ordering information

# Table 3. Ordering information Type number Package Name Description Version BUK4D16-20 DFN2020MD-6 plastic, leadless thermal enhanced ultra thin small outline package with side-wettable flanks (SWF); 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body SOT1220

# 7. Marking

Table 4.	Marking	codes
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Type number	Marking code
BUK4D16-20	6L

20 V, N-channel Trench MOSFET

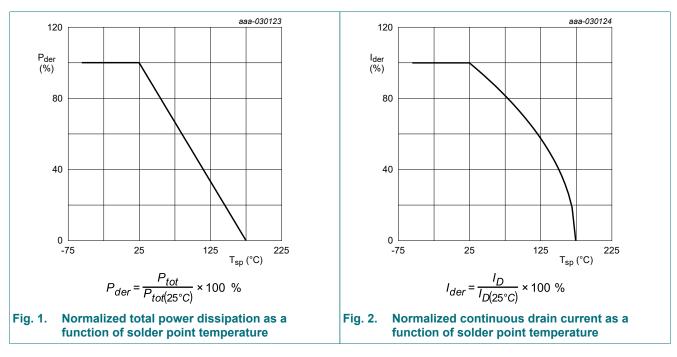
# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

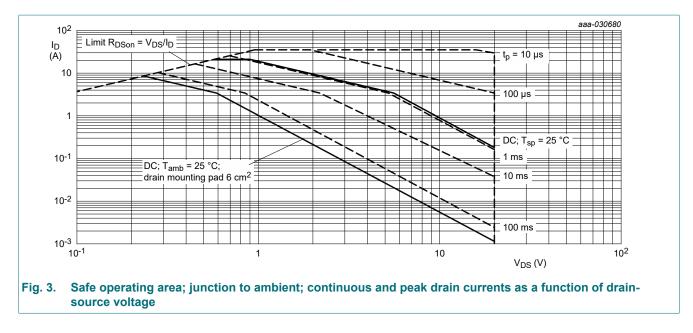
Parameter	Conditions		Min	Мах	Unit
drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
gate-source voltage	_		-12	12	V
drain current	V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 25 °C		-	26	А
	V <sub>GS</sub> = 4.5 V; T <sub>sp</sub> = 100 °C		-	17	А
	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	8.5	А
peak drain current	$T_{sp}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	106	А
total power dissipation	T <sub>sp</sub> = 25 °C		-	19	W
	T <sub>amb</sub> = 25 °C	[1]	-	2	W
junction temperature			-55	175	°C
ambient temperature			-55	175	°C
storage temperature			-65	175	°C
n diode		•			-
source current	T <sub>sp</sub> = 25 °C		-	19	А
	T <sub>amb</sub> = 25 °C	[1]	-	2	А
peak source current	single pulse; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^{\circ}C$		-	75	А
um rating					
electrostatic discharge voltage	НВМ	[2]	-	2000	V
uggedness				·	
non-repetitive drain- source avalanche energy	T <sub>j(init)</sub> = 25 °C; I <sub>D</sub> = 1.3 A; DUT in v avalanche (unclamped)		-	13	mJ
J	drain-source voltage         gate-source voltage         drain current         drain current         total power dissipation         junction temperature         ambient temperature         storage temperature         diode         source current         mrating         electrostatic discharge voltage         uggedness         non-repetitive drain-	$\begin{tabular}{ c c } \hline drain-source voltage & $T_j = 25 \ ^{\circ}C$ \\ \hline gate-source voltage & $V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{amb} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}C$ \\ \hline $V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}C$ \\ \hline $T_{amb} = 25 \ ^{\circ}C$ \\ \hline $T_{amb}$	$\begin{tabular}{ c c c c } \hline \end{tabular} & $T_j = 25\ ^{\circ}C$ & $$$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$ $$$	$\begin{tabular}{ c c c c } \hline \mbox{drain-source voltage} & T_j = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{gate-source voltage} & V_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 100 \ ^{\circ}\ C & -12 \\ \hline \mbox{V}_{GS} = 4.5 \ V; \ T_{sp} = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{T}_{sp} = 25 \ ^{\circ}\ C & -12 \\ \hline \mbox{T}_{amb} = $	$ \begin{array}{ c c c c } \mbox{drain-source voltage} & T_{j} = 25 \ ^{\circ}\ C & & & & & & & & & & & & & & & & & & $

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
 Measured between all pins.



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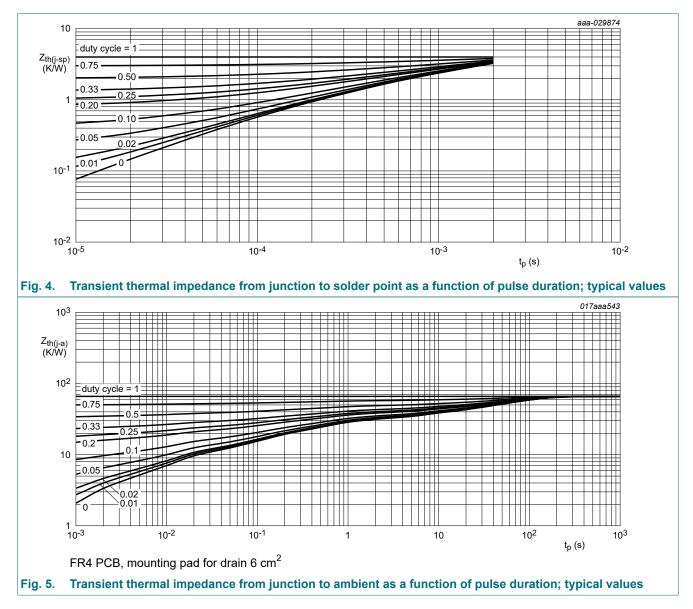
### 20 V, N-channel Trench MOSFET



# 9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	66	76	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	4	8	K/W

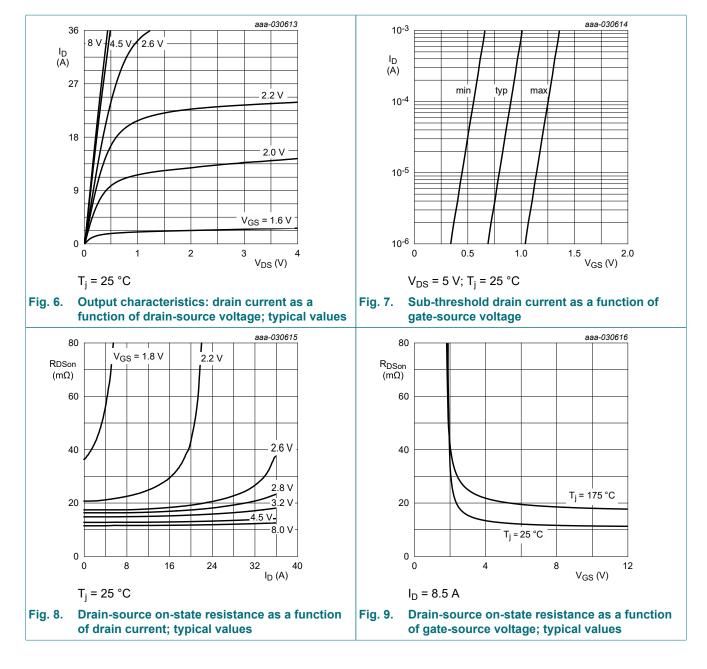
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



# **10. Characteristics**

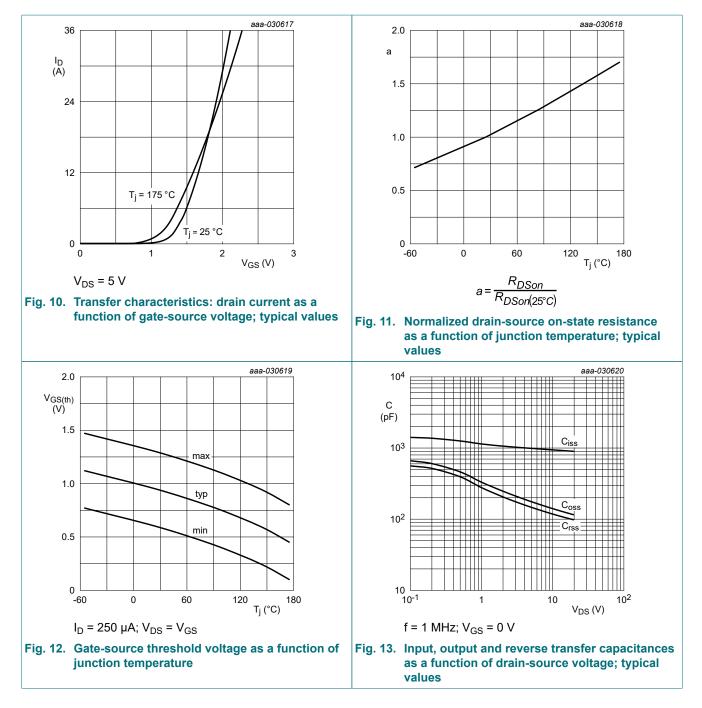
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics	1				
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.6	0.95	1.3	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	20	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 8 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C	-	11	14	mΩ
		V <sub>GS</sub> = 8 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 175 °C	-	19	24	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8.5 A; T <sub>j</sub> = 25 °C	-	13	16	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 3 A; T <sub>j</sub> = 25 °C	-	17	25	mΩ
9fs	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 8.5 A; T <sub>j</sub> = 25 °C	-	14.4	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1.4	-	Ω
Dynamic ch	aracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9 A; V <sub>GS</sub> = 4.5 V;	-	9.8	15	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	931	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	144	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	121	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; I <sub>D</sub> = 9 A; V <sub>GS</sub> = 4.5 V;	-	4	-	ns
r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	7	-	ns
d(off)	turn-off delay time		-	15	-	ns
f	fall time		-	9	-	ns
Source-drai	n diode	,	1			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
rr	reverse recovery time	$I_{S} = 2 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	10	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 10 V; T <sub>j</sub> = 25 °C	-	3	-	nC

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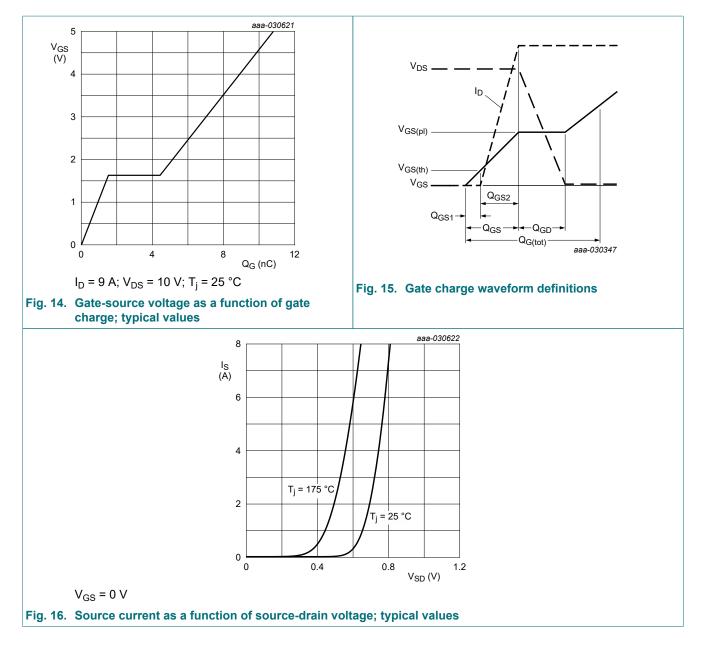


**Product data sheet** 

### 20 V, N-channel Trench MOSFET

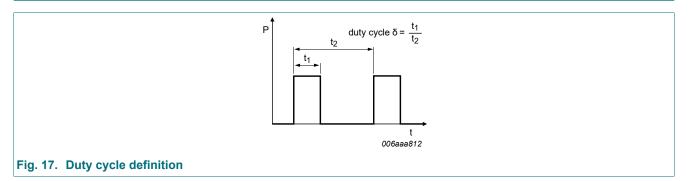


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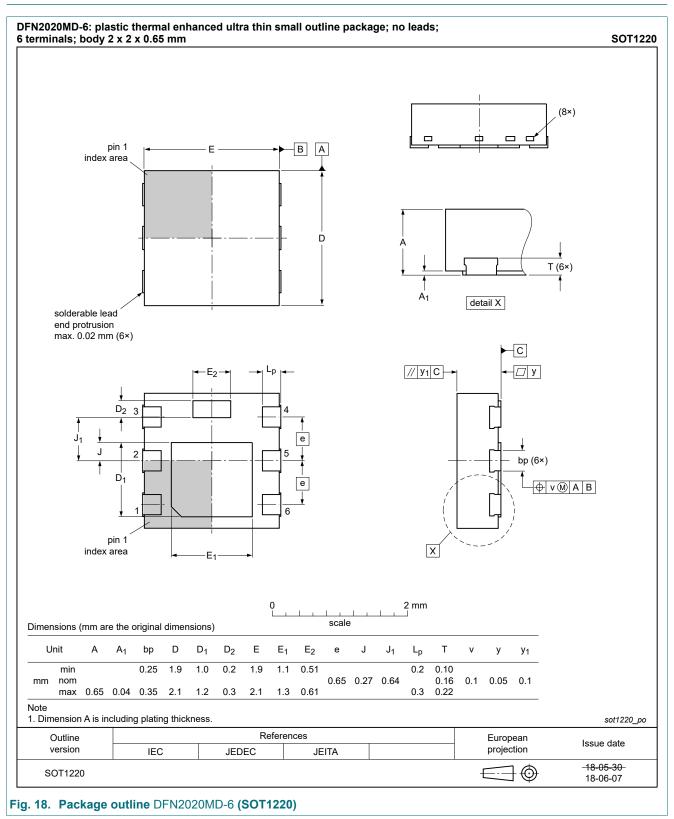
# **11. Test information**



### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

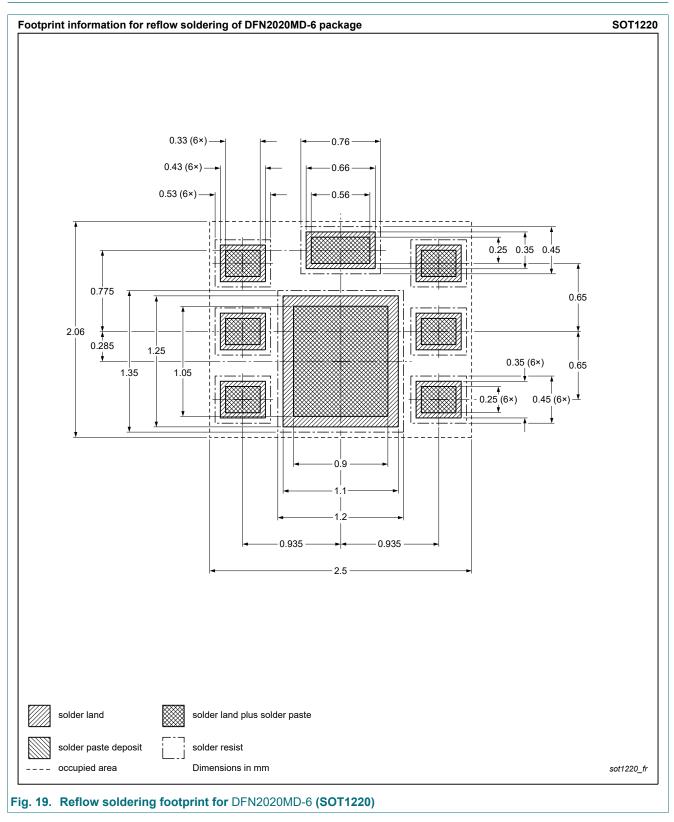
# 12. Package outline



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# 13. Soldering



# 14. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BUK4D16-20 v.3	20210329	Product data sheet	-	BUK4D16-20 v.2			
Modifications:	Chapter "Chara	Chapter "Characteristics": Typo correction at parameter R <sub>DSon</sub>					
BUK4D16-20 v.2	20200709	Product data sheet	-	BUK4D16-20 v.1			
BUK4D16-20 v.1	20200114	Objective data sheet	-	-			

# 15. Legal information

### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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